

Bending Rigidity of Graphene Measurements by Electrostatic Actuation of Buckled Membranes.

Niklas Lindahl¹, Daniel Midtvedt², Johannes Svensson³, Oleg A. Nerushev⁴, Niclas Lindvall⁵,
Andreas Isacson² and Eleanor E. B. Campbell^{4,6,*}

1. Dept. of Physics, University of Gothenburg, Göteborg, SE-41296, Sweden

2. Dept. of Applied Physics, Chalmers University of Technology, Göteborg, SE-41296, Sweden

3. Electrical and Information Technology, Lund University, Lund, SE-22100, Sweden

4. EaStCHEM, School of Chemistry, Edinburgh University, Edinburgh, EH9 3JJ, Scotland

5. Department of Microtechnology and Nanoscience, Chalmers University of Technology, Göteborg, SE-41296, Sweden

6. Division of Quantum Phases and Devices, Dept. of Physics, Konkuk University, Seoul 143-701, Korea

(* Eleanor.Campbell@ed.ac.uk)

The small mass and atomic-scale thickness of graphene membranes make them highly suitable for nanoelectromechanical devices such as e.g. mass sensors, high frequency resonators or memory elements. Although only atomically thick, many of the mechanical properties of graphene membranes can be described by classical continuum mechanics. An important parameter for predicting the performance and linearity of graphene NEMS as well as for describing ripple formation and other properties such as electron scattering mechanisms is the bending rigidity, k . In spite of the importance of this parameter it has so far only been estimated indirectly for monolayer graphene from the phonon spectrum of graphite, estimated from AFM measurements or predicted from *ab initio* calculations or bond-order potential models. We employ a new approach to the experimental determination of k by exploiting the snap-through instability in pre-buckled graphene membranes [1]. We demonstrate the reproducible fabrication of convex buckled graphene membranes by controlling the thermal stress during the fabrication procedure and show the abrupt switching from convex to concave geometry that occurs when electrostatic pressure is applied via an underlying gate electrode. The bending rigidity of bilayer graphene membranes under ambient conditions was determined to be 35.5 ± 0.2 eV. Monolayers have significantly lower k than bilayers.

References

[1] N. Lindahl et al., Nano Letters **12** (2012) 3526